VUSK002R26ANA

Datasheet

General Description

$V_{(BR)DSS}$	$R_{DS(ON)\_max}$	I_D
20V	260mΩ@4.5V	0.75A
	360mΩ@2.5V	
	590mΩ@1.8V	

Symbol

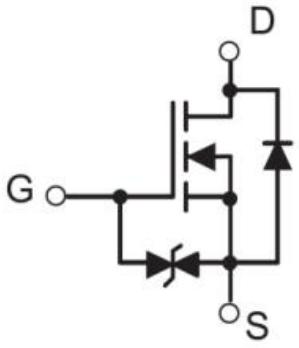
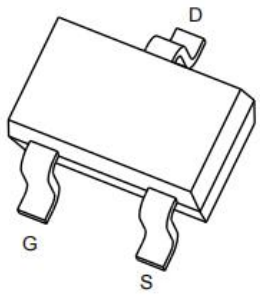


Figure 1 Symbol of VUSK002R26ANA

Features

- Excellent $R_{DS(on)}$ and Low Gate Charge
- Trench FET Power MOSFET
- ESD Protected

Package Type



SOT-523

Figure 2 Package Type of VUSK002R26ANA

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Small Portable Electronics
- Level shift

Ordering Information

Product Name	Package
VUSK002R26ANA	SOT-523

Absolute Maximum Ratings (T_A= 25 ºC, unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	±12	V
Continuous Drain Current	I_D	0.75	A
Pulsed Drain Current[Note1](t=300us)	I_{DM}	3	A
Total Power Dissipation[Note2]	P_D	0.15	W
Junction Temperature	T_J	150	ºC
Storage Temperature	T_{STG}	-55 to 150	ºC

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Ambient[Note1]	$R_{\theta JA}$		653		ºC/W

Electrical Characteristics (T_A= 25 ºC, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D= 250uA	20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}= 20V, V_{GS}=0V			1	uA
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±10V, V_{DS}= 0V			±20	uA
Gate Threshold Voltage[Note3]	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	0.35	0.75	1.1	V
Drain-source on-resistance[Note3]	$R_{DS(on)}$	V_{GS}= 4.5V, I_D= 0.65A		190	260	
		V_{GS}= 2.5V, I_D= 0.55A		260	360	
		V_{GS}= 1.8V, I_D= 0.45A		390	590	
Forward tranconductance[Note3]	g_{FS}	V_{DS}= 10V, I_D= 0.8A		0.9		S
Dynamic Characteristics						
Input Capacitance	C_{ISS}	V_{DS}=16V			120	pF
Output Capacitance	C_{OSS}	V_{GS}=0V			20	pF
Reverse Transfer Capacitance	C_{RSS}	f=1MHz			15	pF
Switching Parameters						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}= 10V		6.7		ns
Turn-on Rise Time	t_r	V_{GEN}=4.5V		4.8		
Turn-off Delay Time	$t_{d(off)}$	I_D= 0.5A		17.3		
Turn-off Fall Time	t_f	R_{GEN}=10Ω		7.4		
Diode Characteristics						
Diode Forward Voltage [Note3]	V_{SD}	V_{GS}=0V, I_S= 0.15A			1.2	V

Notes :

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at T_A=25C.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle≤0.5%.

Typical Performance Characteristics

Figure 3: Transfer Characteristics

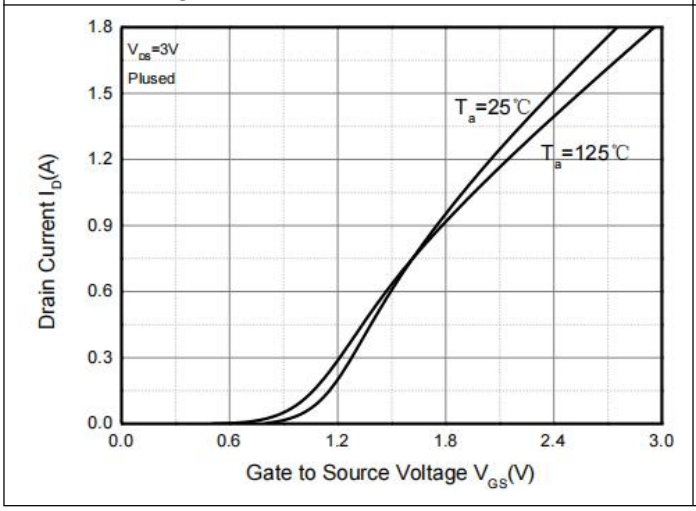


Figure 4: Output Characteristics

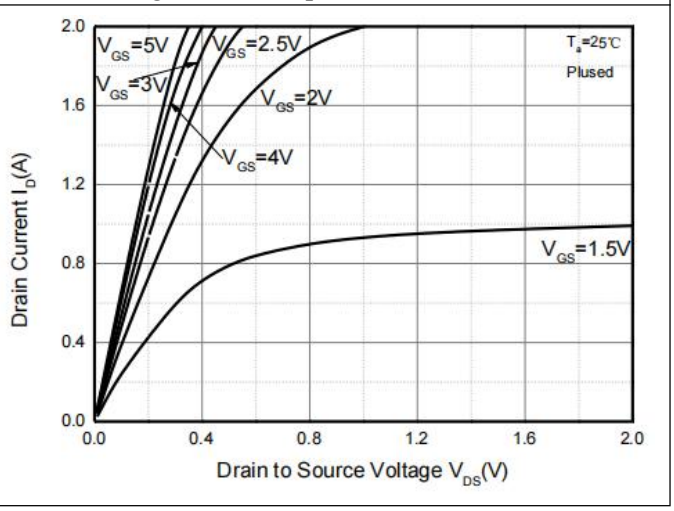


Figure 5: On-Resistance vs. Drain Current

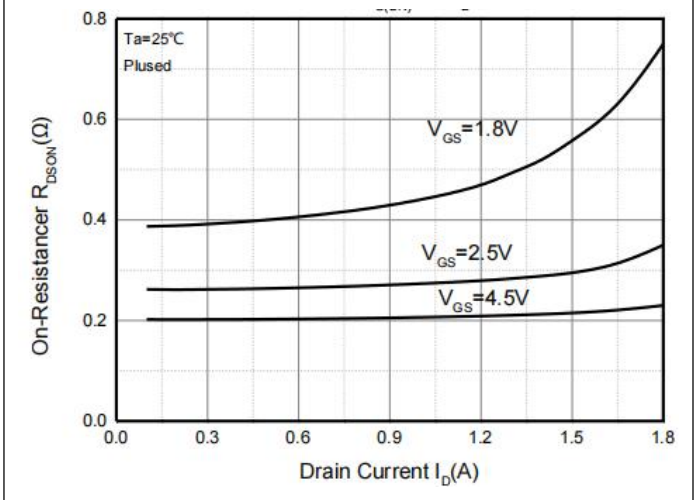


Figure 6: On-Resistance vs. Gate Voltage

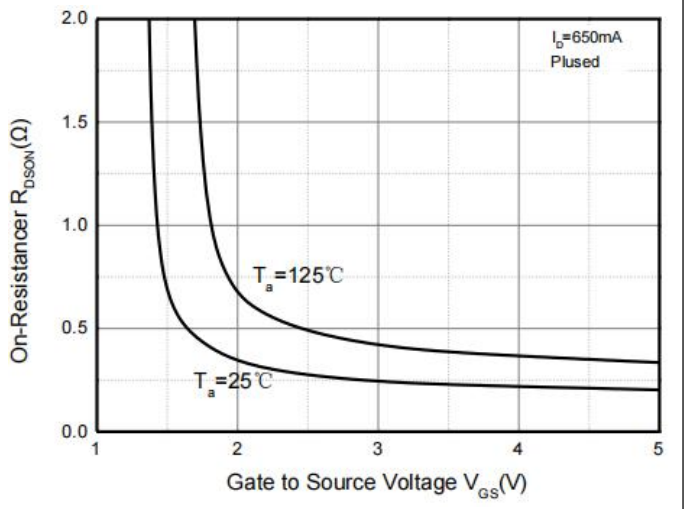


Figure 7: Body Diode Characteristics

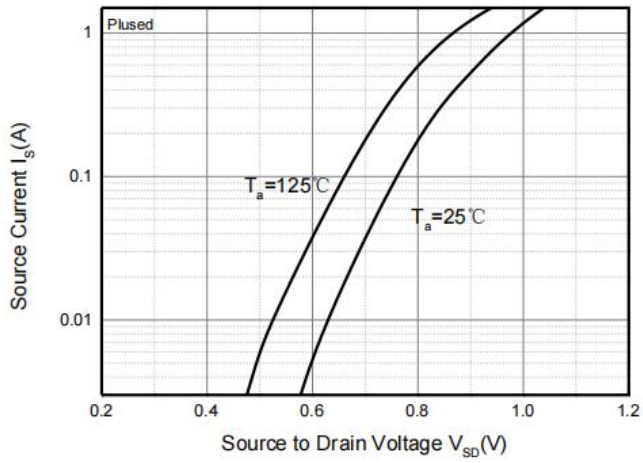
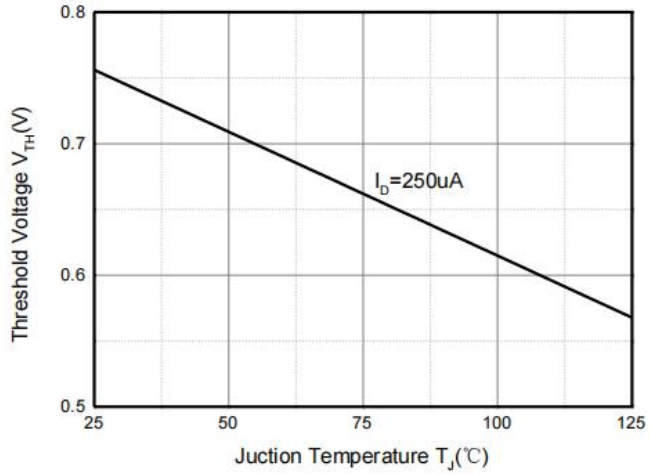
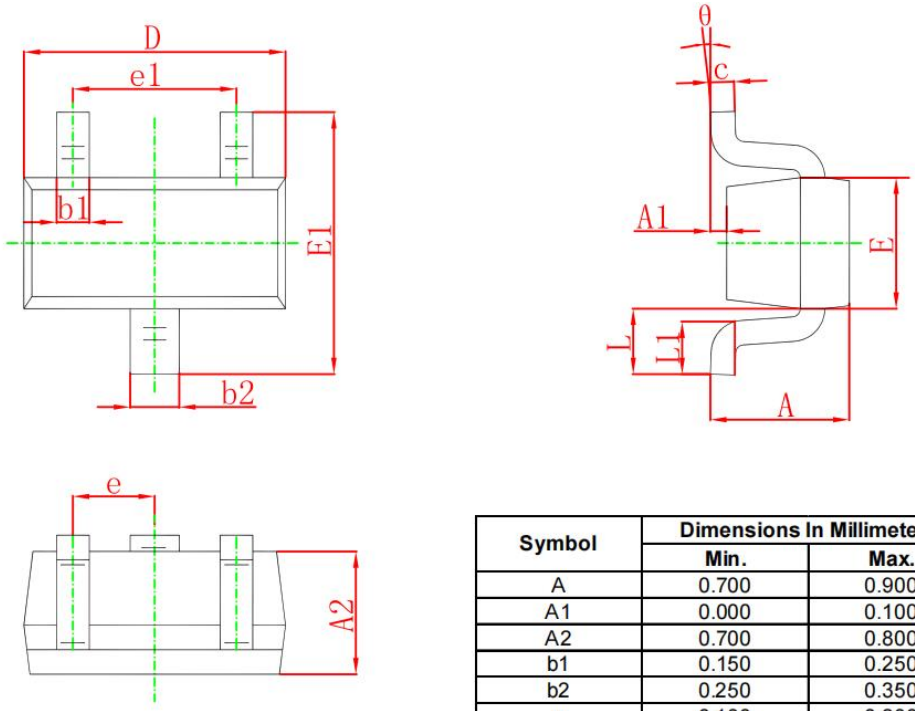


Figure 8: Threshold Voltage



Mechanical Dimensions:

SOT-523 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

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Via-Media Semiconductor Limited Company

http://www.vmdsemi.com

Main Sites:

- **Headquarters**

Hangzhou Via-Media Semiconductor Co., LTD.
1305-1306, Building 71, No. 90, Wensan Road, Xihu District, Hangzhou, Zhejiang Province, P.R. China
Tel: +86-0571-8515 0563

- **Chengdu Office**

Chengdu Winhi Semiconductor Co., LTD.
Floor 15, Building 5, No. 171, Hele 2nd Street, Chengdu, Sichuan Province, P.R. China
Tel: +86-028-8505 0771

- **Shanghai**

Shanghai R&D Center.
1506~1508, Xinyin Building, 888 Yishan Road, Shanghai, P.R of China
Tel: +86- 021-54201999

- **Shenzhen**

Shenzhen Sales Center.
17B, No.1 Phoenix Building, 2008 Shennan Road, Shenzhen, P.R of China
Tel: +86-0755- 82570682

- **Xi'an**

Xi'an R&D Center
1703B, Building A, Greenland Center, Jinye Road, High-Tech Zone, Xi'an, Shaanxi, P.R of China